

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:)	
)	Examiner:
Yuichiro Shindo)	
)	Group Art Unit:
Application No.:)	
)	
Corresponding International Filing No.:)	
PCT/JP2004/015777)	
)	
Filed: Herewith)	
)	
For: HIGH PURITY HAFNIUM,)	
TARGET AND THIN FILM)	
COMPRISING SAID HIGH)	
PURITY HAFNIUM, AND)	
METHOD FOR PRODUCING)	
HIGH PURITY HAFNIUM)	

Mail Stop PCT
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

SECOND PRELIMINARY AMENDMENT

Sir:

Please amend the above-identified patent application as follows.

Amendments to the Specification begin on page two of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page three of this paper.

Remarks begin on page five of this paper.